

# MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

## Digital Transistors (BRT) R1 = 10 kΩ, R2 = 47 kΩ

### PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	6	Vdc

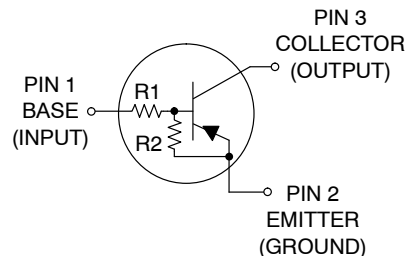
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



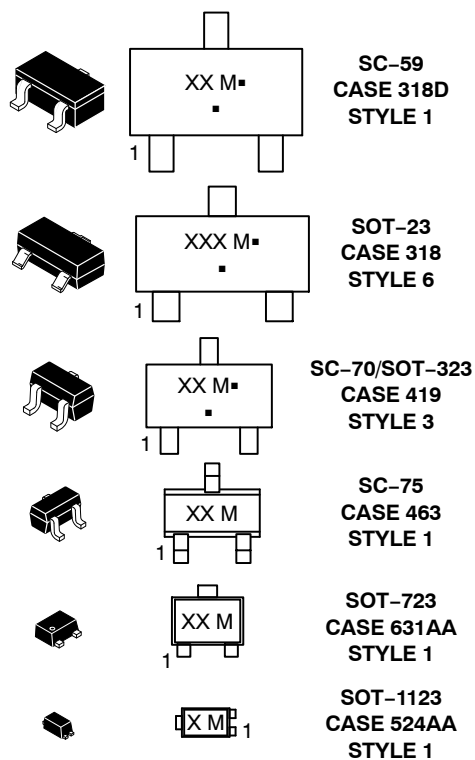
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[www.onsemi.com](http://www.onsemi.com)

#### PIN CONNECTIONS



#### MARKING DIAGRAMS



XXX = Specific Device Code  
M = Date Code\*  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

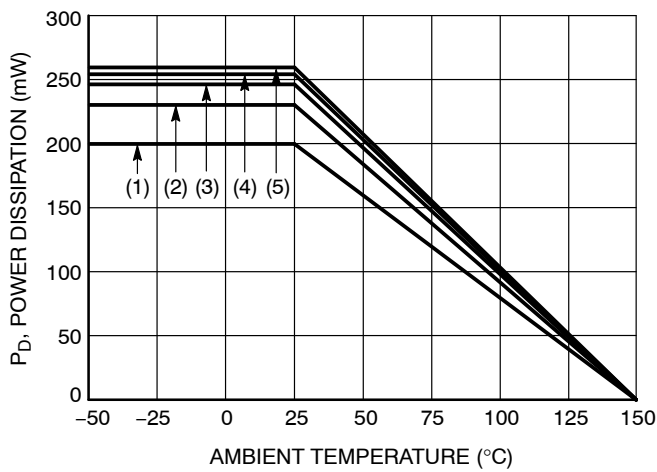
See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

# MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

**Table 1. ORDERING INFORMATION**

Device	Part Marking	Package	Shipping†
MUN2114T1G, SMUN2114T1G*	6D	SC-59	3,000 / Tape & Reel
MMUN2114LT1G, SMMUN2114LT1G*	A6D	SOT-23	3,000 / Tape & Reel
MMUN2114LT3G, NSVMMUN2114LT3G*	A6D	SOT-23	10,000 / Tape & Reel
MUN5114T1G, SMUN5114T1G*	6D	SC-70/SOT-323	3,000 / Tape & Reel
SMUN5114T3G	6D	SC-70/SOT-323	10,000 / Tape & Reel
DTA114YET1G, SDTA114YET1G*	6D	SC-75	3,000 / Tape & Reel
DTA114YM3T5G, NSVDTA114YM3T5G*	6D	SOT-723	8,000 / Tape & Reel
NSBA114YF3T5G	K	SOT-1123	8,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

**Figure 1. Derating Curve**

**MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3**

**Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
<b>THERMAL CHARACTERISTICS (SC-59) (MUN2114)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	230	mW
Derate above $25^\circ\text{C}$		338	mW/°C
		1.8	
		2.7	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	540	°C/W
		370	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	264	°C/W
		287	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C

**THERMAL CHARACTERISTICS (SOT-23) (MMUN2114L)**

Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	246	mW
Derate above $25^\circ\text{C}$		400	mW/°C
		2.0	
		3.2	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	508	°C/W
		311	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	174	°C/W
		208	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C

**THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5114)**

Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	202	mW
Derate above $25^\circ\text{C}$		310	mW/°C
		1.6	
		2.5	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	618	°C/W
		403	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	280	°C/W
		332	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C

**THERMAL CHARACTERISTICS (SC-75) (DTA114YE)**

Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	200	mW
Derate above $25^\circ\text{C}$		300	mW/°C
		1.6	
		2.4	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	600	°C/W
		400	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C

**THERMAL CHARACTERISTICS (SOT-723) (DTA114YM3)**

Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	260	mW
Derate above $25^\circ\text{C}$		600	mW/°C
		2.0	
		4.8	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	480	°C/W
		205	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
- FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

# MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

**Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
<b>THERMAL CHARACTERISTICS (SOT-1123) (NSBA114YF3)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$  Derate above $25^\circ\text{C}$	(Note 3) (Note 4) (Note 3) (Note 4)	$P_D$  254 297 2.0 2.4	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{\theta JA}$  493 421	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	(Note 3)	$R_{\theta JL}$  193	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
- FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 3. ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Base Cutoff Current ( $V_{CB} = 50\text{ V}, I_E = 0$ )	$I_{CBO}$	-	-	100	nAdc
Collector-Emitter Cutoff Current ( $V_{CE} = 50\text{ V}, I_B = 0$ )	$I_{CEO}$	-	-	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0\text{ V}, I_C = 0$ )	$I_{EBO}$	-	-	0.2	mAdc
Collector-Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}, I_E = 0$ )	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) ( $I_C = 2.0\text{ mA}, I_B = 0$ )	$V_{(BR)CEO}$	50	-	-	Vdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain (Note 5) ( $I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$ )	$h_{FE}$	80	140	-	
Collector - Emitter Saturation Voltage (Note 5) ( $I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$ )	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0\text{ V}, I_C = 100\ \mu\text{A}$ )	$V_{i(off)}$	-	0.7	0.5	Vdc
Input Voltage (on) ( $V_{CE} = 0.2\text{ V}, I_C = 1.0\text{ mA}$ )	$V_{i(on)}$	1.4	0.9	-	Vdc
Output Voltage (on) ( $V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$ )	$V_{OL}$	-	-	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$ )	$V_{OH}$	4.9	-	-	Vdc
Input Resistor	R1	7.0	10	13	k $\Omega$
Resistor Ratio	$R_1/R_2$	0.17	0.21	0.25	

- Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq 2\%$ .

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS  
MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3

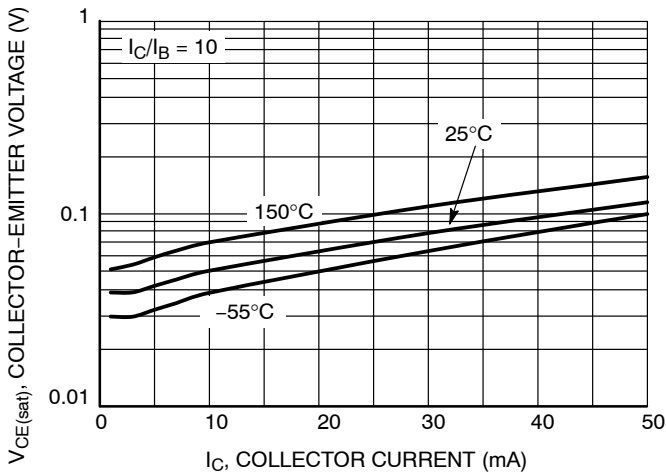


Figure 2.  $V_{CE(sat)}$  vs.  $I_C$

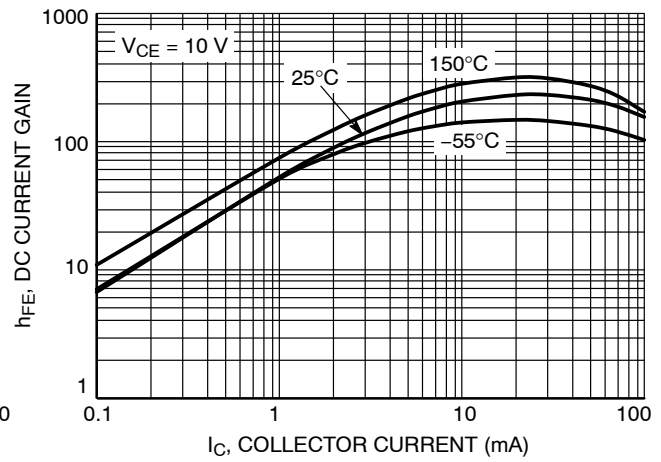


Figure 3. DC Current Gain

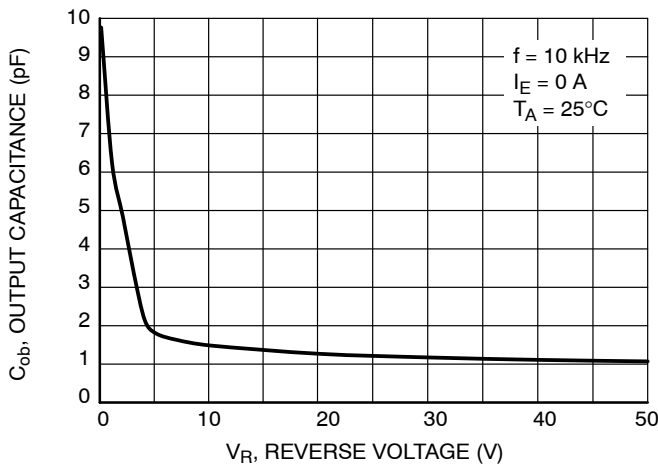


Figure 4. Output Capacitance

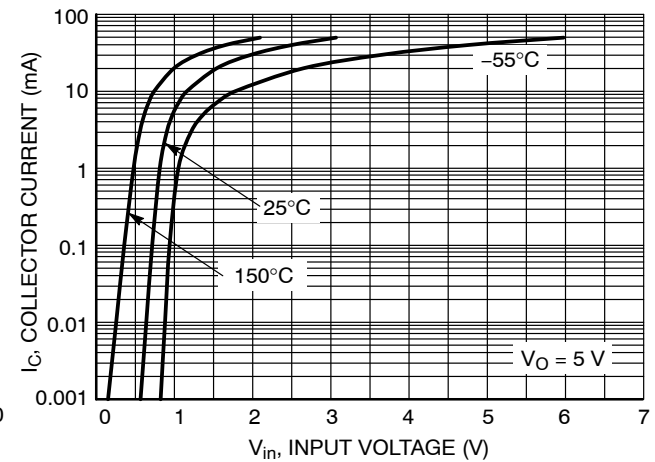


Figure 5. Output Current vs. Input Voltage

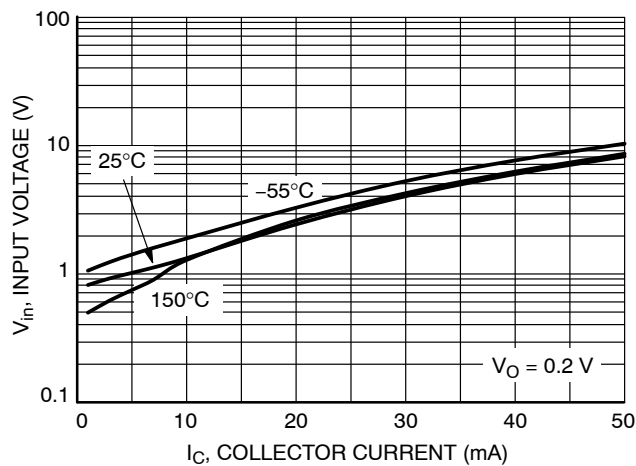


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS  
NSBA114YF3

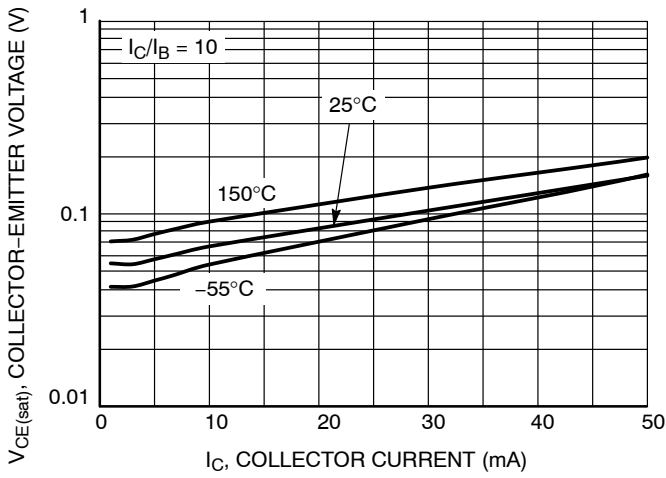


Figure 7.  $V_{CE(sat)}$  vs.  $I_C$

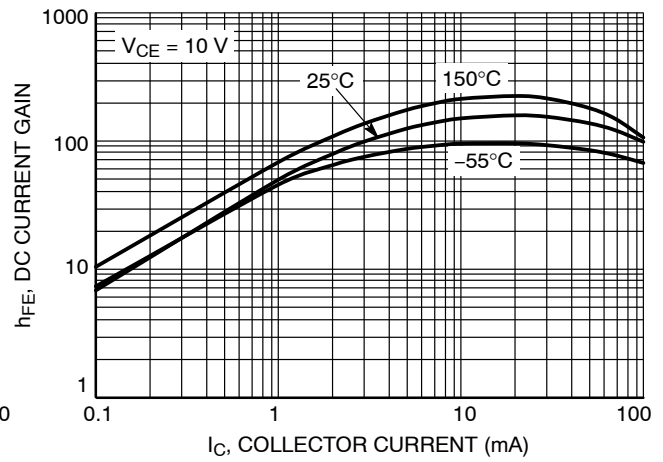


Figure 8. DC Current Gain

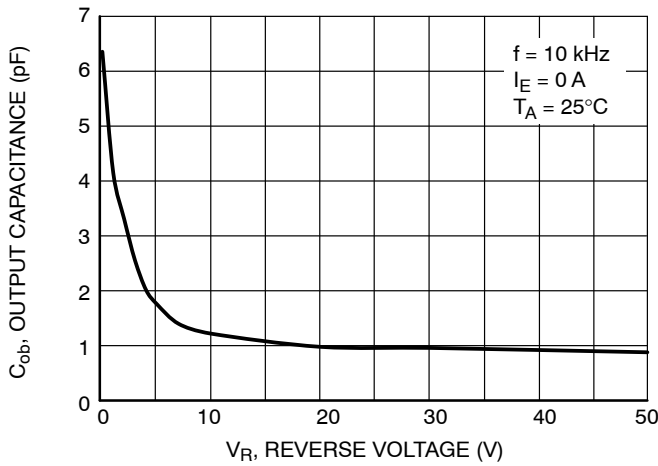


Figure 9. Output Capacitance

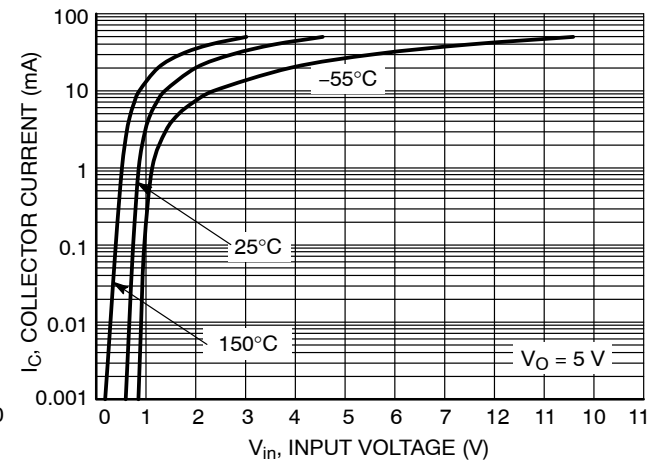


Figure 10. Output Current vs. Input Voltage

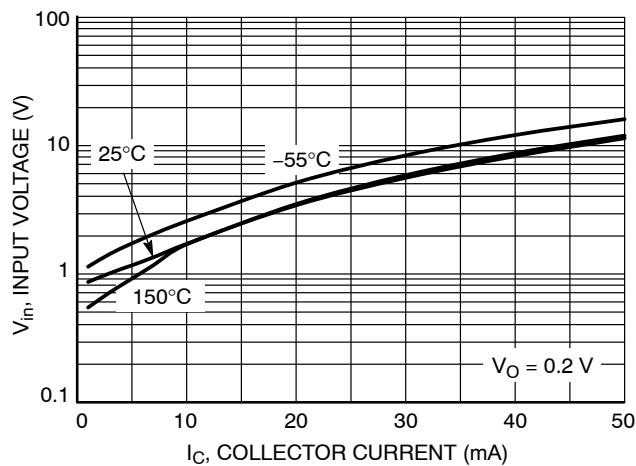
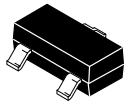


Figure 11. Input Voltage vs. Output Current

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

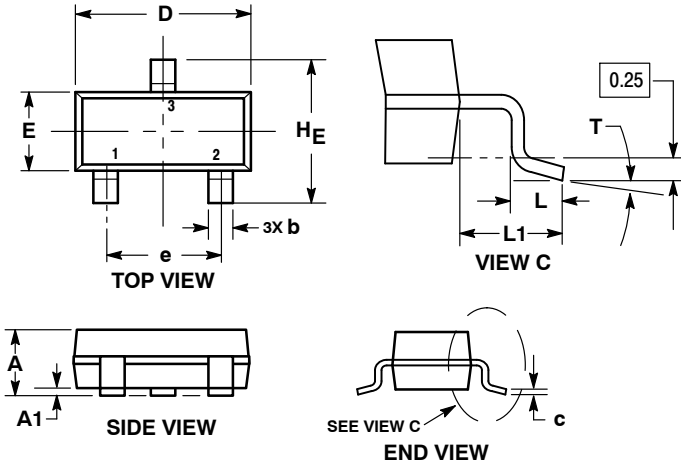
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**SOT-23 (TO-236)**  
CASE 318-08  
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

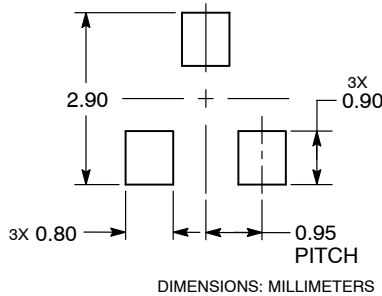


**NOTES:**

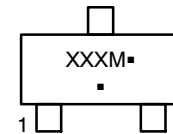
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- |   |   |   |  |
|---|---|---|--|
| STYLE 1 THRU 5:<br>CANCELLED                                | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR       | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE           | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE      |
| STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          | STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE          | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE      |
| STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE         |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN           | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT         | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE          |
| STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION | STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE          |

<b>DOCUMENT NUMBER:</b>	<b>98ASB42226B</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SOT-23 (TO-236)</b>	<b>PAGE 1 OF 1</b>

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

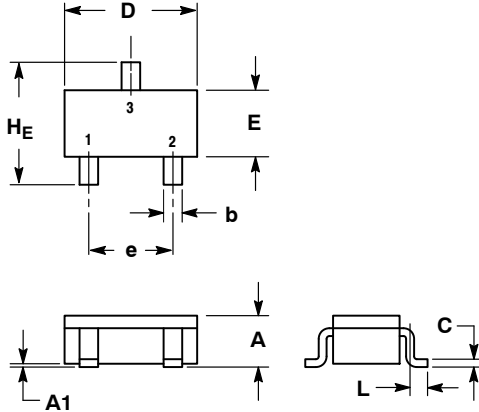
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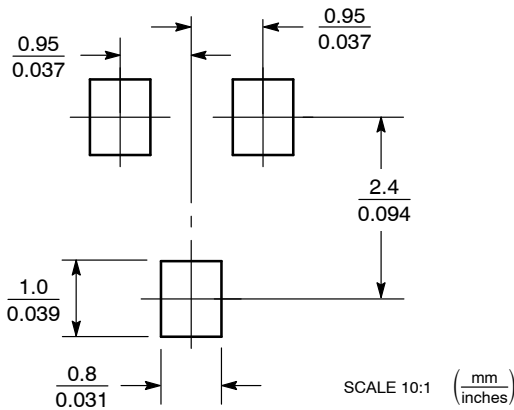
SC-59  
CASE 318D-04  
ISSUE H

DATE 28 JUN 2012

SCALE 2:1



### SOLDERING FOOTPRINT\*

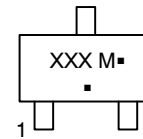


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

### GENERIC MARKING DIAGRAM



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package\*

(\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 2:  
PIN 1. ANODE  
2. N.C.  
3. CATHODE

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. N.C.  
3. ANODE

STYLE 5:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

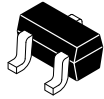
STYLE 6:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE/CATHODE

DOCUMENT NUMBER:	98ASB42664B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC-59	PAGE 1 OF 1

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



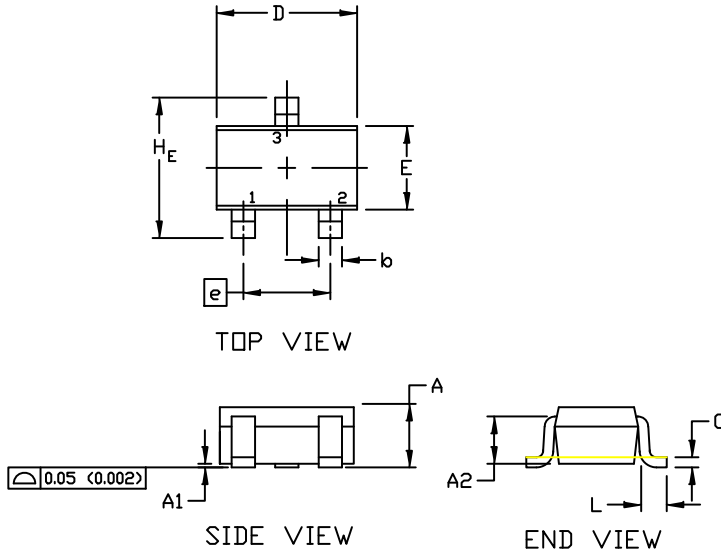
SCALE 4:1

SC-70 (SOT-323)  
CASE 419  
ISSUE P

DATE 07 OCT 2021

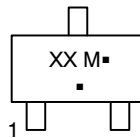
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH



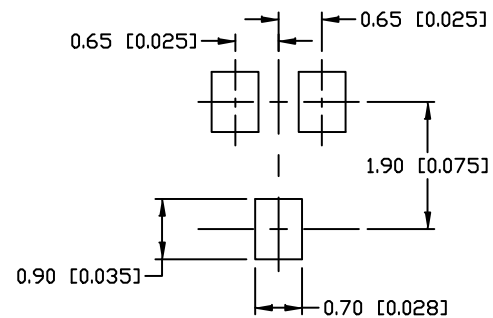
DIM	MILLIMETERS			INCHES		
	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H <sub>E</sub>	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC  
MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

- |   |   |   |  |   |
|---|---|---|--|---|
| STYLE 1:<br>CANCELLED                                 | STYLE 2:<br>PIN 1. ANODE<br>2. N.C.<br>3. CATHODE     | STYLE 3:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE       | STYLE 5:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          |
| STYLE 6:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR | STYLE 7:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 8:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN      | STYLE 9:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 10:<br>PIN 1. CATHODE<br>2. ANODE<br>3. ANODE-CATHODE |
|   |   |   |  | STYLE 11:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     |

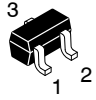
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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

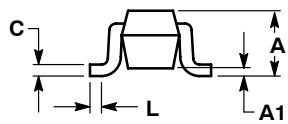
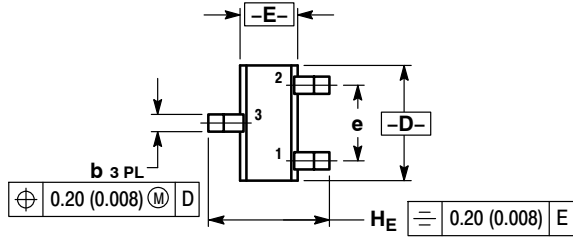
ON Semiconductor®



SC-75/SOT-416  
CASE 463-01  
ISSUE G

DATE 07 AUG 2015

SCALE 4:1



STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 2:  
PIN 1. ANODE  
2. N/C  
3. CATHODE

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

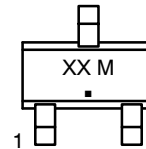
STYLE 5:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.060	0.063	0.067

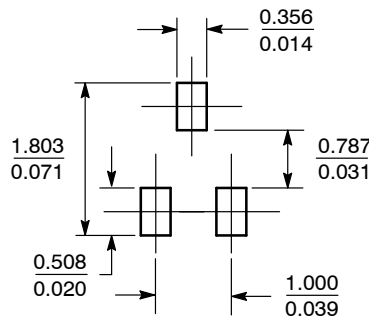
GENERIC MARKING DIAGRAM\*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

SOLDERING FOOTPRINT\*



SCALE 10:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

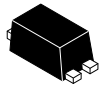
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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

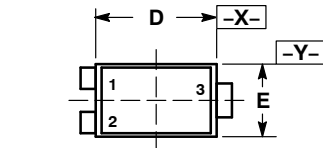
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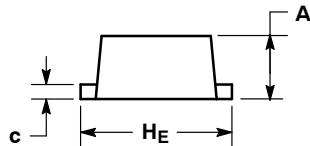
SCALE 8:1

SOT-1123  
CASE 524AA  
ISSUE C

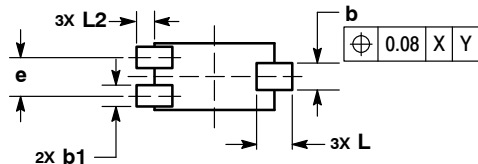
DATE 29 NOV 2011



TOP VIEW

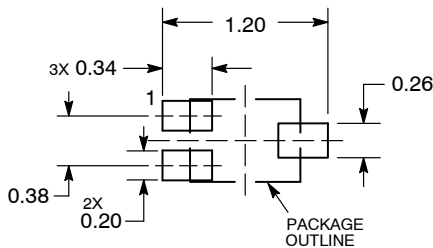


SIDE VIEW



BOTTOM VIEW

### SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

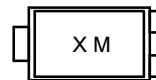
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.34	0.40
b	0.15	0.28
b1	0.10	0.20
c	0.07	0.17
D	0.75	0.85
E	0.55	0.65
e	0.35	0.40
HE	0.95	1.05
L	0.185	REF
L2	0.05	0.15

### GENERIC MARKING DIAGRAM\*



X = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "•", may or may not be present.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

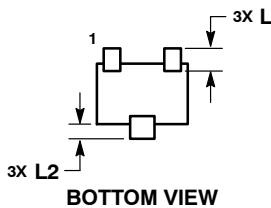
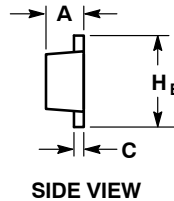
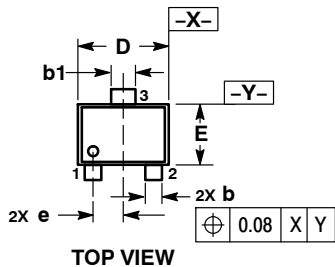
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SCALE 4:1

**SOT-723**  
CASE 631AA-01  
ISSUE D

DATE 10 AUG 2009

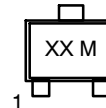


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

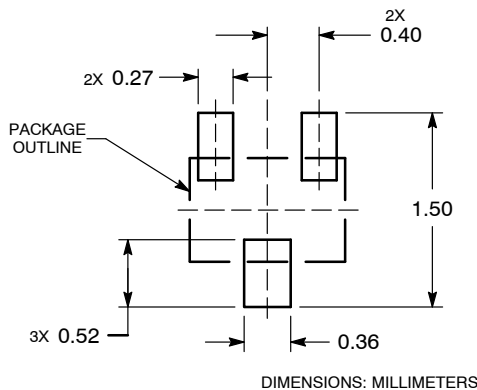
**GENERIC MARKING DIAGRAM\***



XX = Specific Device Code  
M = Date Code

- |   |  |  |  |  |
|---|--|--|--|--|
| STYLE 1:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 2:<br>PIN 1. ANODE<br>2. N/C<br>3. CATHODE | STYLE 3:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE | STYLE 5:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN |
|---|--|--|--|--|

**RECOMMENDED SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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